

MJE205 (SILICON)

MJE205K

MEDIUM-POWER NPN SILICON TRANSISTORS

... for use as an output device in complementary audio amplifiers up to 20-Watts music power per channel.

- High DC Current Gain — $h_{FE} = 25-100 @ I_C = 2.0 \text{ A}$
- Thermopad High-Efficiency Compact Package
- Complementary to PNP MJE 105, MJE105K
- Choice of Packages — MJE205-Case 90
MJE205K-Case 199

5 AMPERE POWER TRANSISTORS

NPN SILICON

50 VOLTS
65 WATTS

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	50	Vdc
Collector-Base Voltage	V_{CB}	50	Vdc
Emitter-Base Voltage	V_{EB}	4.0	Vdc
Collector Current	I_C	5.0	Adc
Base Current	I_B	2.5	Adc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_{DT}	65 0.522	Watts W/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	θ_{JC}	1.92	$^\circ\text{C/W}$

† Safe Area Curves are indicated by Figure 1. Both limits are applicable and must be observed.

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

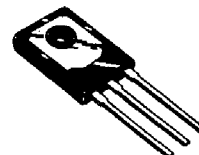
Collector-Emitter Breakdown Voltage ‡ ($I_C = 100 \text{ mAdc}, I_B = 0$)	$BV_{CEO}^\pm$	50	—	Vdc
Collector Cutoff Current ($V_{CB} = 50 \text{ Vdc}, I_E = 0$) ($V_{CB} = 50 \text{ Vdc}, I_E = 0, T_C = 150^\circ\text{C}$)	I_{CBO}	—	0.1 2.0	mAdc
Emitter Cutoff Current ($V_{BE} = 4.0 \text{ Vdc}, I_C = 0$)	I_{EBO}	—	1.0	mAdc

ON CHARACTERISTICS

DC Current Gain ($I_C = 2.0 \text{ Adc}, V_{CE} = 2.0 \text{ Vdc}$)	h_{FE}	25	100	—
Base-Emitter Voltage ($I_C = 2.0 \text{ Adc}, V_{CE} = 2.0 \text{ Vdc}$)	V_{BE}	—	1.2	Vdc

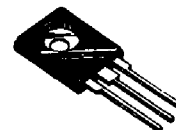
‡ Pulse Test: Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle $\leq 2.0\%$.

MJE 205

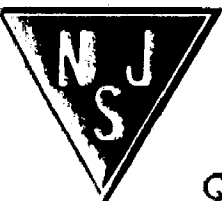


CASE 90-05

MJE205K



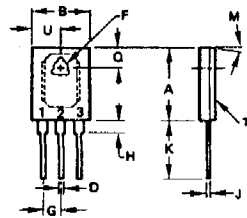
CASE 199-04



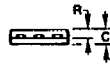
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Quality Semi-Conductors

MJE205



STYLE 2:
PIN 1. EMITTER
2. COLLECTOR
3. BASE

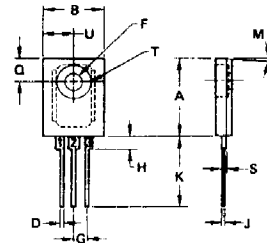


DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	16.13	16.38	0.635	0.645
B	12.57	12.83	0.495	0.505
C	3.18	3.43	0.125	0.135
D	1.08	1.24	0.043	0.049
E	3.51	3.76	0.138	0.148
F	4.22 BSC		0.166 BSC	
G	2.67	2.92	0.105	0.115
H	0.813	0.864	0.032	0.034
I	15.11	16.38	0.595	0.645
J	90 TYP		90 TYP	
K	4.70	4.95	0.185	0.195
L	1.91	2.16	0.075	0.085
M	6.22	6.48	0.245	0.255

NOTE:
1. LEADS WITHIN .005" RAD OF TRUE POSITION (TP) AT MMC

CASE 90-05

MJE205K



STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. EMITTER

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	16.08	16.33	0.633	0.643
B	12.57	12.83	0.495	0.505
C	3.18	3.43	0.125	0.135
D	0.51	0.76	0.020	0.030
E	3.61	3.86	0.142	0.152
F	2.54 BSC		0.100 BSC	
G	2.67	2.92	0.105	0.115
H	0.43	0.69	0.017	0.027
I	14.73	14.99	0.580	0.590
J	2.18	2.41	0.085	0.095
K	36 TYP		36 TYP	
L	1.47	1.73	0.058	0.068
M	4.78	5.03	0.188	0.198
N	1.81	2.16	0.075	0.085
O	0.81	0.86	0.032	0.034
P	6.99	7.24	0.275	0.285
Q	6.22	6.48	0.245	0.255

1. DIM "G" IS TO CENTER LINE OF LEADS.

CASE 199-04